

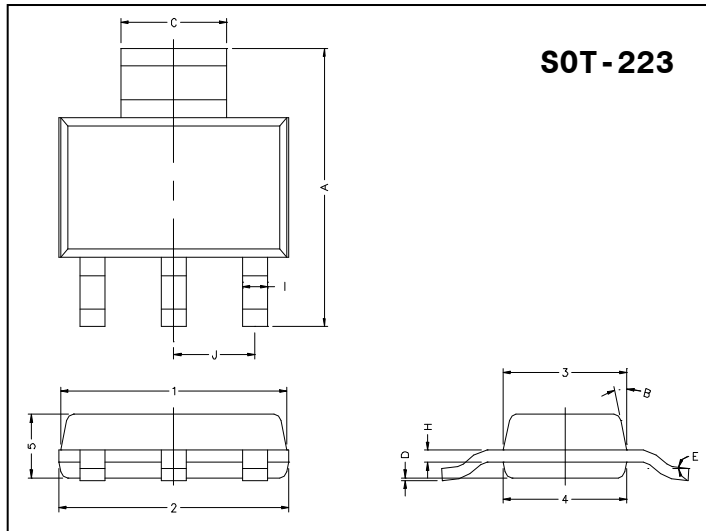
GL5551

NPN EPITAXIAL PLANAR TRANSISTOR

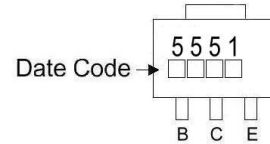
Description

The GL5551 is designer for general purpose applications requiring high breakdown voltages.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CB0}	180	V
Collector to Emitter Voltage	V _{CEO}	160	V
Emitter to Base Voltage	V _{EB0}	6	V
Collector Current	I _C	600	mA
Total Power Dissipation	P _D	1.5	W

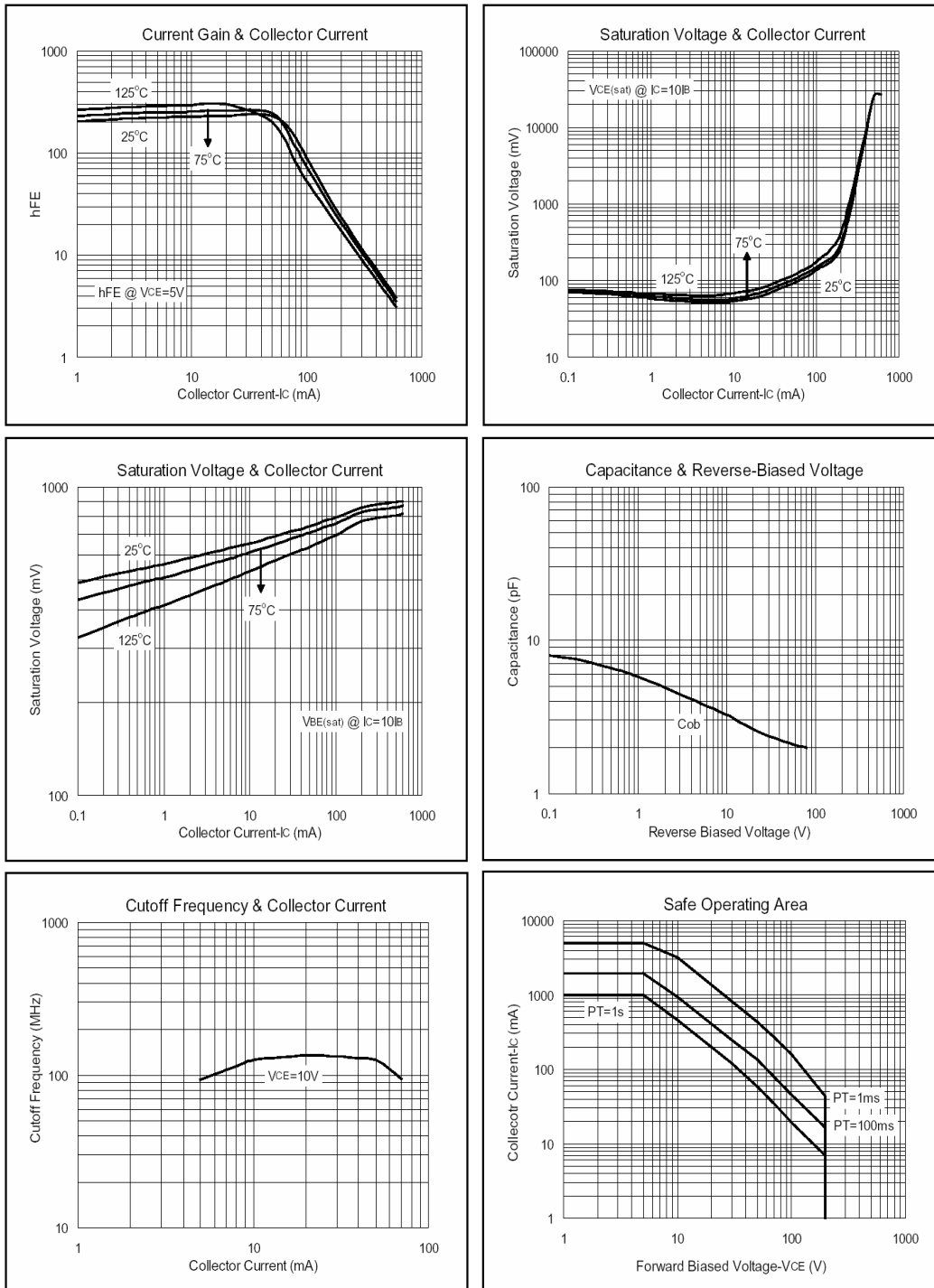
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CB0}	180	-	-	V	I _C =100μA, I _E =0
V _{CEO}	160	-	-	V	I _C =1.0mA, I _B =0
V _{EB0}	6	-	-	V	I _E =10μA, I _C =0
I _{CB0}	-	-	50	nA	V _{CB} =120V, I _E =0
I _{EB0}	-	-	50	nA	V _{EB} =4V, I _C =0
V _{CE(sat)1}	-	-	0.15	V	I _C =10mA, I _B =1.0mA
V _{CE(sat)2}	-	-	0.2	V	I _C =50mA, I _B =5mA
V _{BE(sat)1}	-	-	1	V	I _C =10mA, I _B =1mA
V _{BE(sat)2}	-	-	1	V	I _C =50mA, I _B =5mA
h _{FE1}	80	-	-		V _{CE} =5V, I _C =1mA
h _{FE2}	80	160	400		V _{CE} =5V, I _C =10mA
h _{FE3}	50	-	-		V _{CE} =5V, I _C =50mA
f _T	100	-	300	MHz	V _{CE} =10V, I _C =10mA, f=100MHz
C _{ob}	-	-	6	pF	V _{CB} =10V, I _E =0, f=1MHz

Classification Of hFE

Rank	A	N	C
Range	80 - 200	100 - 250	160 - 400

Characteristics Curve



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